

# isc Silicon NPN Power Transistor

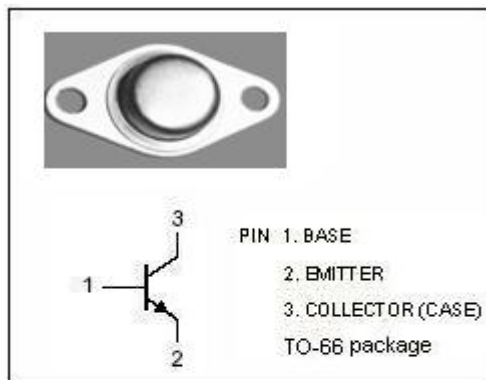
# BUX77

## DESCRIPTION

- Continuous Collector Current- $I_C = 5A$
- Collector Power Dissipation-  
:  $P_C = 40W @ T_C = 25^\circ C$
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 80V(\text{Min})$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

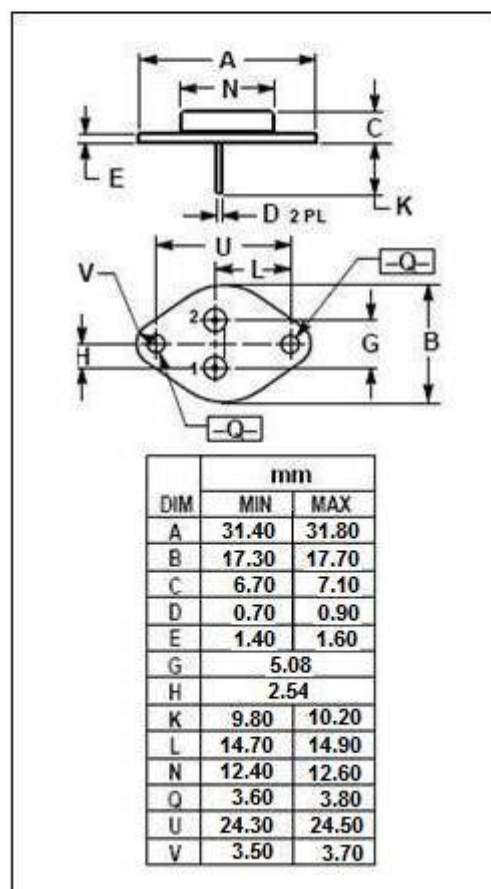
## APPLICATIONS

- Designed for use in switching regulators and general purpose power amplifiers.



## ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	5	A
$I_B$	Base Current-Continuous	0.8	A
$P_C$	Collector Power Dissipation@ $T_C = 25^\circ C$	40	W
$T_J$	Junction Temperature	200	$^\circ C$
$T_{stg}$	Storage Temperature	-65~200	$^\circ C$



## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	4.4	$^\circ C/W$

**isc Silicon NPN Power Transistor****BUX77****ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	80		V
V <sub>CEs</sub>	Collector-Emitter Voltage	I <sub>C</sub> = 2mA; V <sub>BE</sub> = 0	100		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A		1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A		1.3	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 60V; I <sub>B</sub> = 0		10	μ A
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0 V <sub>CB</sub> = 80V; I <sub>E</sub> = 0, T <sub>C</sub> =150°C		0.5 150	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0		0.5	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	70		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	50		120
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	30		
h <sub>FE-4</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V; T <sub>C</sub> = -40°C	25		

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